



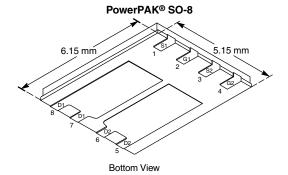
# **Dual N-Channel 30 V (D-S) MOSFET**

PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)		
30	0.022 at V <sub>GS</sub> = 10 V	10		
	0.030 at V <sub>GS</sub> = 4.5 V	8.5		

## **FEATURES**

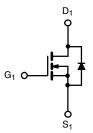
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET<sup>®</sup> Power MOSFET
- 100 % R<sub>g</sub> Tested
- Compliant to RoHS Directive 2002/95/EC



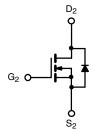


Ordering Information: Si7844DP-T1-E3 (Lead (Pb)-free)

Si7844DP-T1-GE3 (Lead (Pb)-free and Halogen-free)



N-Channel MOSFET



N-Channel MOSFET

<b>ABSOLUTE MAXIMUM RATINGS</b> (T <sub>A</sub> = 25 °C, unless otherwise noted)						
Parameter		Symbol	10 s	Steady State	Unit	
Drain-Source Voltage		V <sub>DS</sub>	30		V	
Gate-Source Voltage		V <sub>GS</sub>	± 20		V	
Continuous Drain Current (T <sub>.I</sub> = 150 °C) <sup>a</sup>	T <sub>A</sub> = 25 °C	- I <sub>D</sub>	10	6.4	Α	
	T <sub>A</sub> = 70 °C		8.0	5.1		
Pulsed Drain Current		I <sub>DM</sub>	20		^	
Continuous Source Current (Diode Conduction) <sup>a</sup>		I <sub>S</sub>	2.9	1.1	I	
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C	P <sub>D</sub>	3.5	1.4	W	
Waximum Fower Dissipation	T <sub>A</sub> = 70 °C		2.2	0.9		
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150		°C	
Soldering Recommendations (Peak Temperature) <sup>b, c</sup>			260			

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient <sup>a</sup>	t ≤ 10 s	- R <sub>thJA</sub>	26	35	°C/W
Maximum Junction-to-Ambient	Steady State		60	85	
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	3.9	5.5	

#### Notes:

- a. Surface mounted on 1" x 1" FR4 board.
- b. See solder profile (<a href="www.vishay.com/ppg?73257">www.vishay.com/ppg?73257</a>). The PowerPAK SO-8 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- c. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

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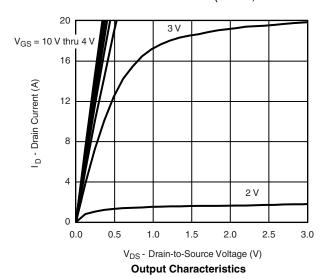
Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static			•	•		
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	0.8		2.4	V
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 100	nA
Zero Gate Voltage Drain Current		V <sub>DS</sub> = 30 V, V <sub>GS</sub> = 0 V			1	
	IDSS	$V_{DS} = 30 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55 ^{\circ}\text{C}$			5	μΑ
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, V_{GS} = 10 \text{ V}$	20			Α
Drain-Source On-State Resistance <sup>a</sup>	Б	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 10 A		0.018	0.022	Ω
	R <sub>DS(on)</sub>	$V_{GS} = 4.5 \text{ V}, I_D = 8.5 \text{ A}$		0.024	0.030	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 10 A		22		S
Diode Forward Voltage <sup>a</sup>	$V_{SD}$	I <sub>S</sub> = 2.9 A, V <sub>GS</sub> = 0 V		0.75	1.2	V
Dynamic <sup>b</sup>						
Total Gate Charge	Qg			13	20	nC
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 15 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 10 \text{ A}$		2		
Gate-Drain Charge	$Q_{gd}$			2.7		
Gate Resistance	$R_g$		0.5		3.2	Ω
Turn-On Delay Time	t <sub>d(on)</sub>			8	16	
Rise Time	t <sub>r</sub>	$V_{DD} = 15 \text{ V}, R_L = 15\Omega$		10	20	ns
Turn-Off Delay Time	t <sub>d(off)</sub>	$I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 6 \Omega$		21	40	
Fall Time	t <sub>f</sub>			10	20	
Source-Drain Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 2.9 A, dI/dt = 100 A/μs		40	80	

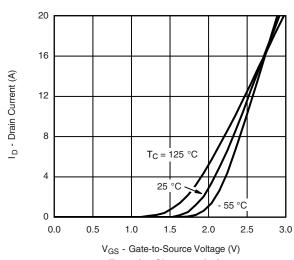
#### Notes:

- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

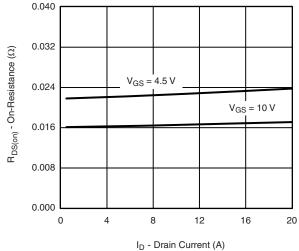


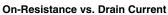


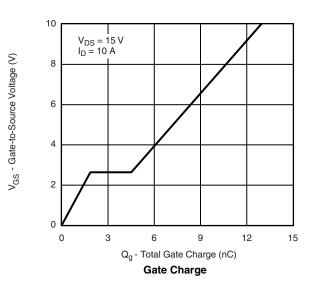


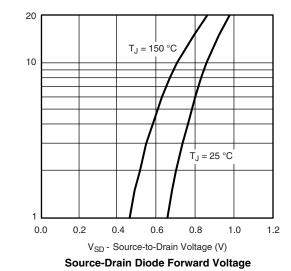


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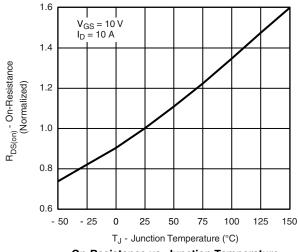




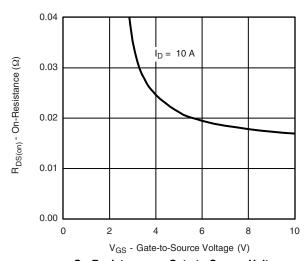


1000 800 C<sub>iss</sub> 600 400 C<sub>rss</sub> 0 6 12 18 24 30

V<sub>DS</sub> - Drain-to-Source Voltage (V) **Capacitance** 



On-Resistance vs. Junction Temperature



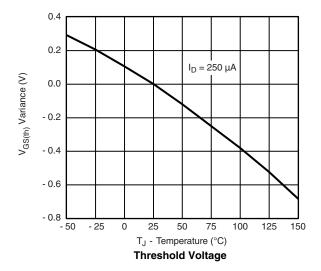
On-Resistance vs. Gate-to-Source Voltage

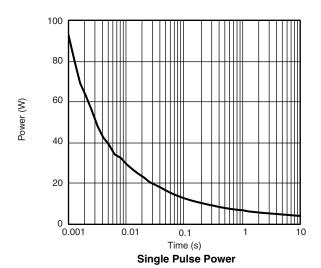
Is - Source Current (A)

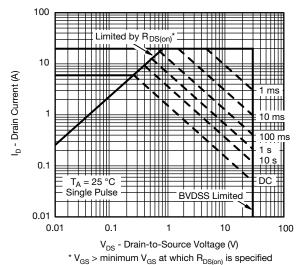
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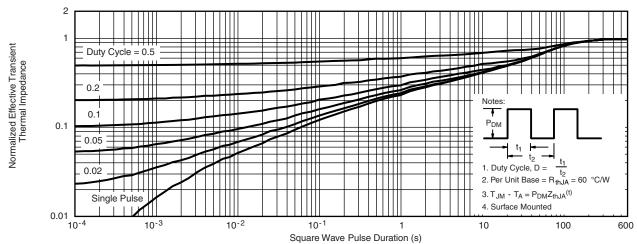
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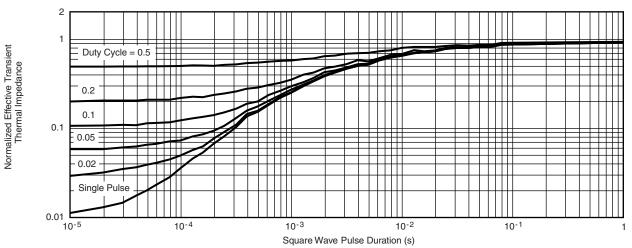




Normalized Thermal Transient Impedance, Junction-to-Ambient



## TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="https://www.vishay.com/ppg271328">www.vishay.com/ppg271328</a>.



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Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.

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